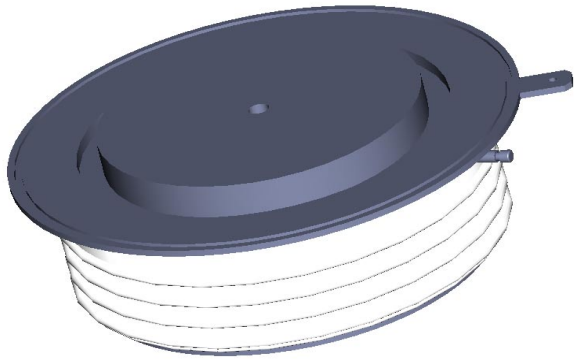
Green Power Solutions srl
Via Greto di Cornigliano 6R - 16152 Genova , Italy

Phone: +39-010-659 1869
Fax: +39-010-659 1870
Web: www.gpsemi.it
E-mail: info@gpsemi.it



GPTP1270

PHASE CONTROLLED SCR

High reliability operation
Electroplating applications
Resistance welding applications

BLOCKING VOLTAGE UP TO	**800**	**V**
AVERAGE CURRENT	**2700**	**A**
SURGE CURRENT	**32**	**kA**

BLOCKING CHARACTERISTICS

Characteristic		Conditions	Value	
V_{RRM}	Repetitive peak reverse voltage		800	V
V_{RSM}	Non-repetitive peak reverse voltage		900	V
V_{DRM}	Repetitive peak off-state voltage		800	V
I_{DRM}	Repetitive peak off-state current, max.	V_{DRM}, single phase, half wave, Tj = Tjmax	100	mA
I_{RRM}	Repetitive peak reverse current, max.	V_{RRM}, single phase, half wave, Tj = Tjmax	100	mA

ON-STATE CHARACTERISTICS

$I_{T(AV)}$	Average on-state current	Sine wave,180° conduction, Th = 55 °C	2700	A
$I_{T(RMS)}$	R.M.S. on-state current	Sine wave,180° conduction, Th = 55 °C	4241	A
I_{TSM}	Surge on-state current	Non rep. half sine wave, 50 Hz, V_R = 0 V, $T_j = T_{jmax}$	32	kA
I^2t	I² t for fusing coordination		5120	kA²s
$V_{T(TO)}$	Threshold voltage	$T_j = T_{jmax}$	0,85	V
r_T	On-state slope resistance	$T_j = T_{jmax}$	0,122	mΩ
V_{TM}	Peak on-state voltage, max	On-state current I_T = 2000 A , Tj = 25 °C	1,15	V
I_H	Holding current, max	T_j = 25 °C	300	mA
I_L	Latching current, typ	T_j = 25 °C	700	mA

TRIGGERING CHARACTERISTICS

V_{GT}	Gate trigger voltage	T_j = 25 °C, V_D = 5 V	2,5	V
I_{GT}	Gate trigger current	T_j = 25 °C, V_D = 5 V	300	mA
V_{GD}	Non-trigger voltage	V_D = 67% V_{RRM}, $T_j = T_{jmax}$	0,25	V
P_{GM}	Peak gate power dissipation	Pulse width 100 µs	150	W
$P_{G(AV)}$	Average gate power dissipation		2	W
I_{FGM}	Peak gate current		10	A
V_{FGM}	Peak gate voltage (forward)		10	V
V_{RGM}	Peak gate voltage (reverse)		12	V

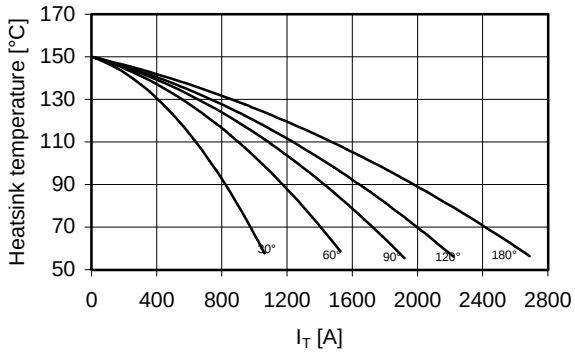
SWITCHING CHARACTERISTICS

di/dt	Critical rate of rise of on-state current	$T_j = T_{jmax}$	200	A/µs
dV/dt	Critical rate of rise of off-state voltage	$T_j = T_{jmax}$	500	V/µs
t_q	Turn-off time, typ	$T_j = T_{jmax}$, I_T = 1000 A, di/dt = -20 A/µs		µs
		VR = 50 V, VD = 67% VDRM, dV/dt = 20 V/µs		

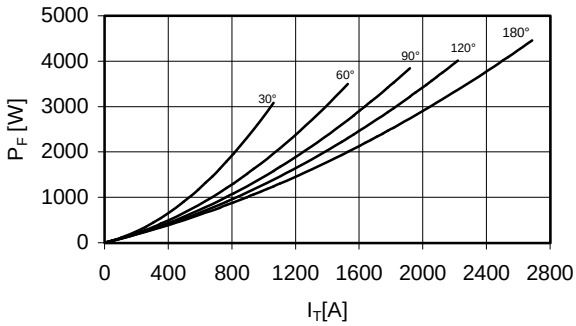
THERMAL AND MECHANICAL CHARACTERISTICS

$R_{th(j-c)}$	Thermal resistance (junction to case)	Double side cooled	0,015	°C/W
$R_{th(c-h)}$	Thermal resistance (case to heatsink)	Double side cooled	0,006	°C/W
T_{jmax}	Max operating junction temperature		150	°C
T_{stg}	Storage temperature		-40 / 150	°C
F	Clamping force ± 5%		23	kN
	Mass		500	g

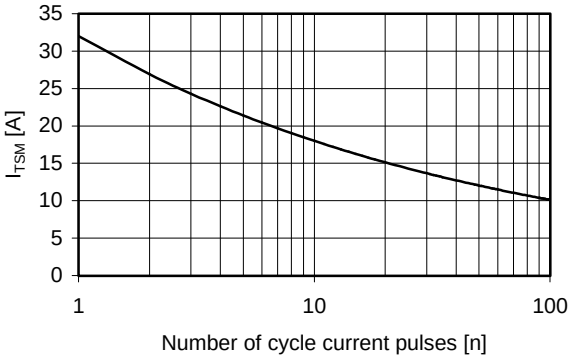
Current rating - sine wave



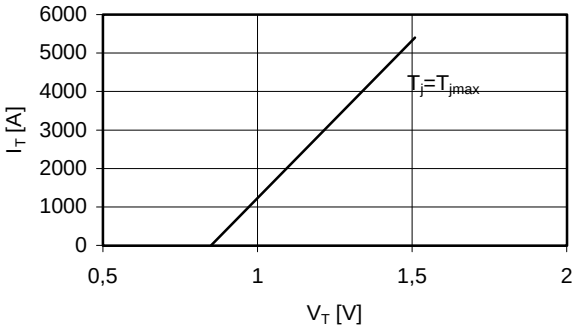
Power loss - sine wave



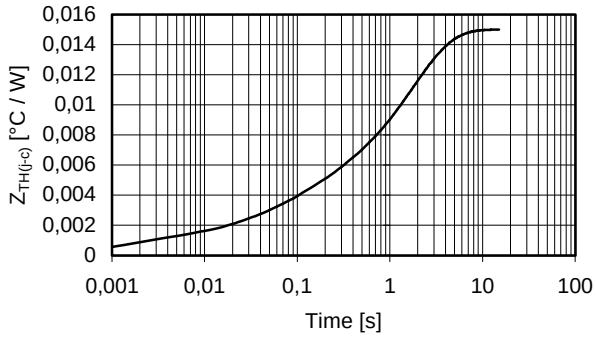
Maximum surge current
d.s. cooled

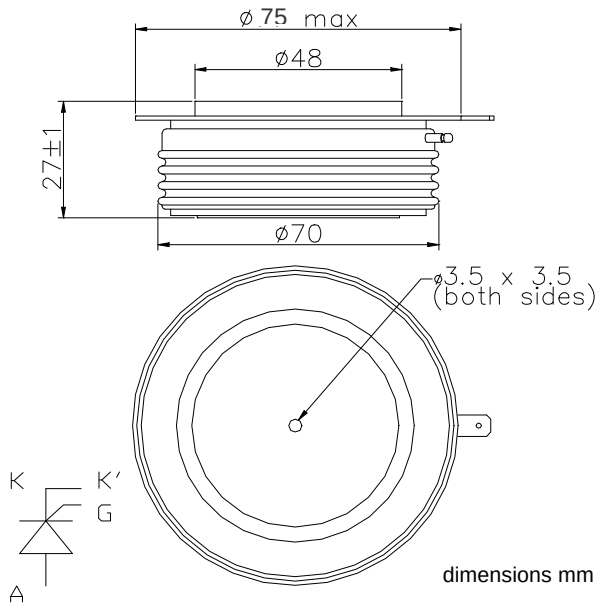


On-state voltage drop



Thermal impedance (j-c)





dimensions mm